

$R_{DS(ON)}$ (at $V_{GS}=-2.5V$) 850 mohm
 $R_{DS(ON)}$ (at $V_{GS}=-1.8V$) 1200 mohm
 $R_{DS(ON)}$ (at $V_{GS}=-1.8V$) 2000 mohm
 ESD Protected Up to 2.0KV (HBM)

General Description

Trench Power LV MOSFET technology
 High Density Cell Design for Low $R_{DS(ON)}$
 High Speed switching

Applications

Interfacing, Logic switch
 Load switch
 Power management

Γ-363

SO1

Absolute Maximum Ratings ($T_A=25$ unless otherwise noted)

Parameter	Symbol	Maximum	Unit
Drain-source Voltage	V_{DS}	-20	V
Gate-source Voltage	V_{GS}	12	V
Drain Current	I_D	$T_A=25$ Steady State	-0.5
		$T_A=70$ Steady State	-0.4
Pulsed Drain Current ^A	I_{DM}	-2.6	A
Total Power Dissipation @ $T_A=25$ Steady State	P_D	0.15	W
Thermal Resistance Junction-to-Ambient @ Steady State ^B	R_{JA}	833	W
Junction and Storage Temperature Range	T_J, T_{STG}	-55 +150	

YJL3139KADW	F2e 39KAe 3000e 30000e	e	"			
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Electrical Characteristics ($T_J=25$



Typical Performance Characteristics

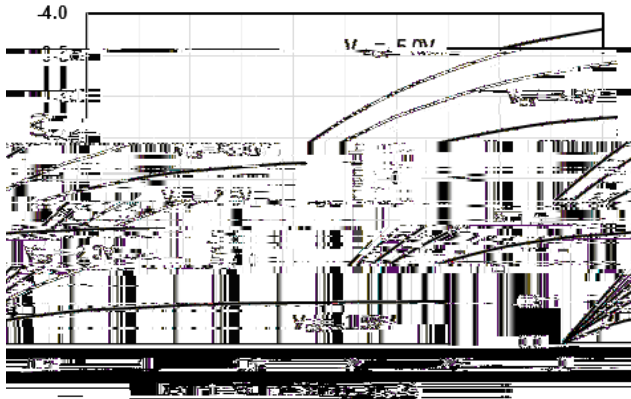


Figure1. Output Characteristics

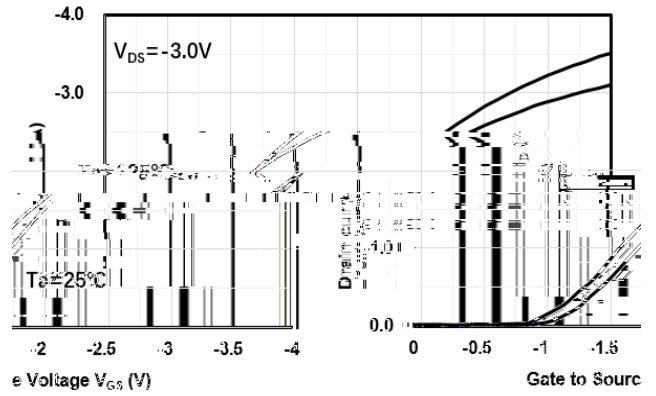


Figure2. Transfer Characteristics

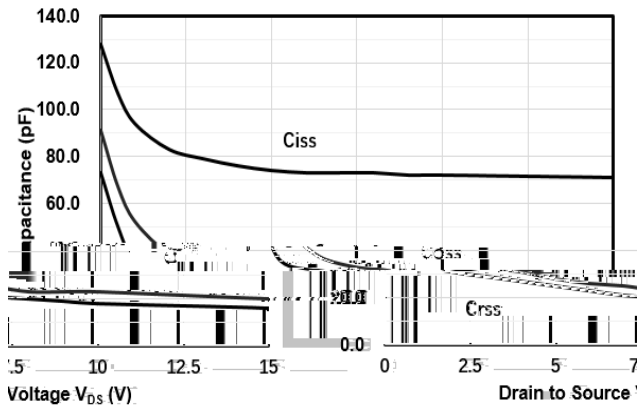


Figure3. Capacitance Characteristics

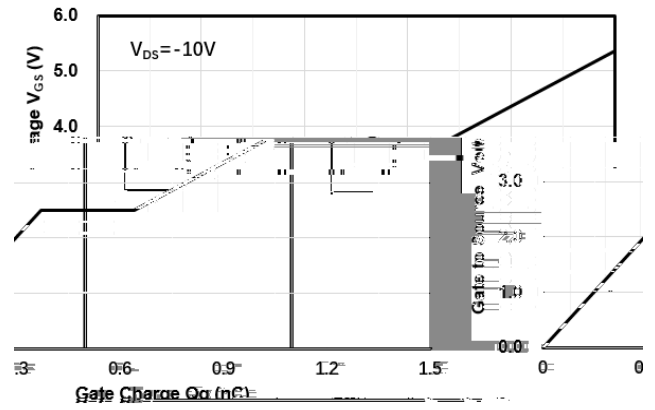


Figure4. Gate Charge

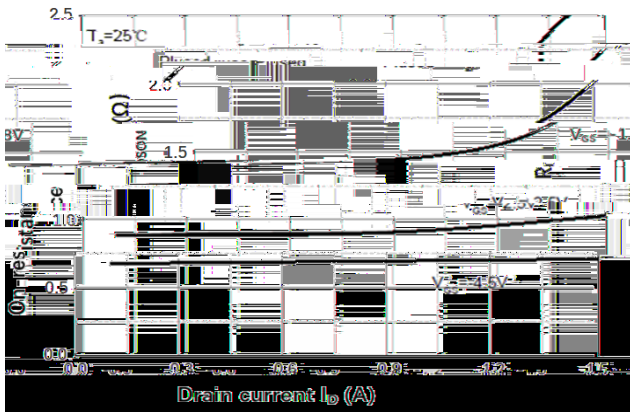


Figure5. Drain-Source on Resistance

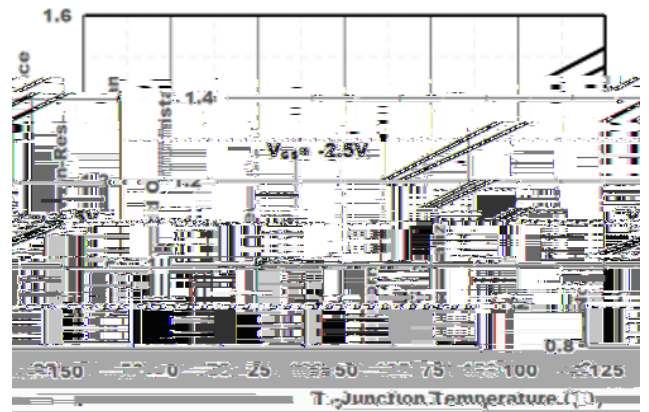


Figure6. Drain-Source on Resistance

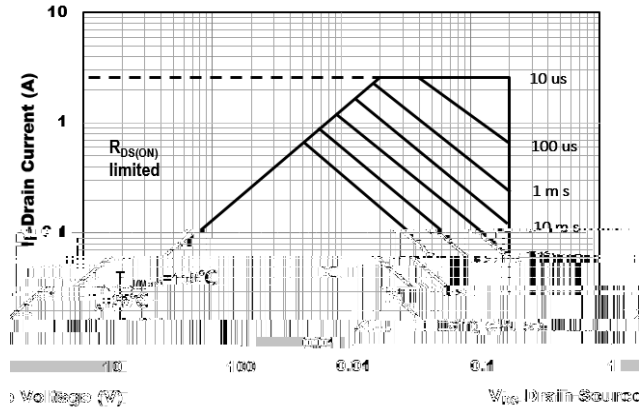


Figure7. Safe Operation Area

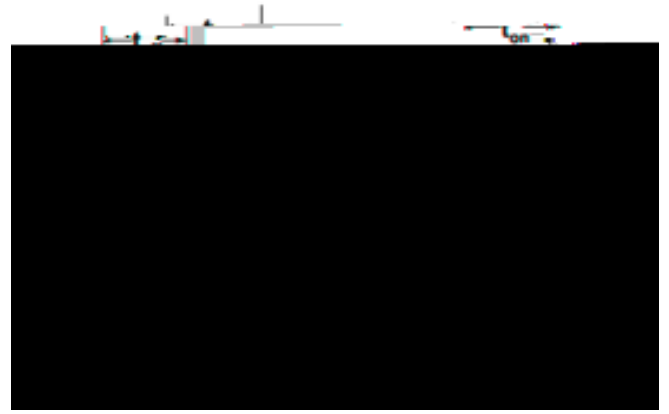


Figure8. Switching wave

< - / . \$ ' :

v 6 2 7

3 D F N D J H L Q I R U P D W L R Q

